

Features

- Ultra Low Leakage: nA Level
- Low Clamping Voltage
- Response time is typically < 1 ns

Die Top-View



Circuit Diagram



Wafer Information

Item	Description	Unit
Wafer size	6	inch
Wafer thickness	150±10	μm
Die Size (Include scribe line)	206*206	μm
Bond Pad Opening	72*72	μm
Scribe line width	50	μm
Gross dies per wafer	357	K pcs
Top metal for wire bond	4μm AlSiCu	
Back side metal	TiNiAgSn	
Passivation thickness		μm

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	56	W
ESD per IEC 61000-4-2 (Air)	VESD	±20	kV
ESD per IEC 61000-4-2 (Contact)		±20	
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}				3.3	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	4.2			V
Reverse Leakage Current	I_R	$V_{RWM} = 3.3\text{V}$			0.1	μA
Clamping Voltage	V_C	$I_{PP} = 1\text{A}$ (8 x 20 μs pulse)			10	V
Clamping Voltage	V_C	$I_{PP} = 4\text{A}$ (8 x 20 μs pulse)			14	V
Junction Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$		0.45	0.60	pF

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